

LMX2335/LMX2336/LMX2337 PLLatinum[™] Dual Frequency Synthesizer for RF Personal Communications

LMX2335 1.1 GHz/1.1 GHz LMX2336 2.0 GHz/1.1 GHz 550 MHz/550 MHz LMX2337

General Description

The LMX2335, LMX2336 and LMX2337 are monolithic, integrated dual frequency synthesizers, including two high frequency prescalers, and are designed for applications requiring two RF phase-lock loops. They are fabricated using National's ABiC IV silicon BiCMOS process.

The LMX2335/36/37 contains two dual modulus prescalers. A 64/65 or a 128/129 prescaler can be selected for each RF synthesizer. A second reference divider chain is included in the IC for improved system noise. LMX2335/36/37, which employ a digital phase locked loop technique, combined with a high quality reference oscillator and loop filters, provide the tuning voltages for voltage controlled oscillators to generate very stable low noise RF local oscillator signals.

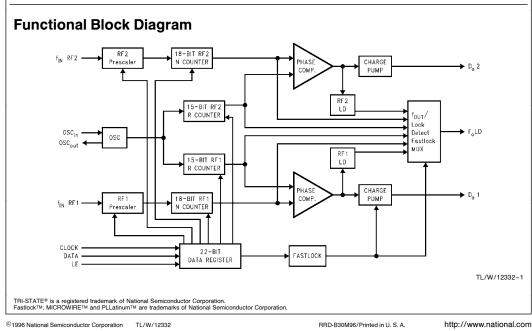
Serial data is transferred into the LMX2335/36/37 via a three wire interface (Data, Enable, Clock). Supply voltage can range from 2.7V to 5.5V. The LMX2335/36/37 feature very low current consumption; LMX2335/37 -10 mA at 3V, LMX2336 - 13 mA at 3V. The LMX2335/37 are available in both a JEDEC SO and TSSOP 16-pin surface mount plastic package. The LMX2336 is available in a TSSOP 20-pin surface mount plastic package.

Features

- 2.7V to 5.5V operation
- Low current consumption
- Selectable powerdown mode:
- $I_{CC} = 1 \ \mu A \ (typ)$
- Dual modulus prescaler: 64/65 or 128/129
- Selectable charge pump TRI-STATE® mode
- Selectable charge pump current levels ■ Selectable Fastlock[™] mode

Applications

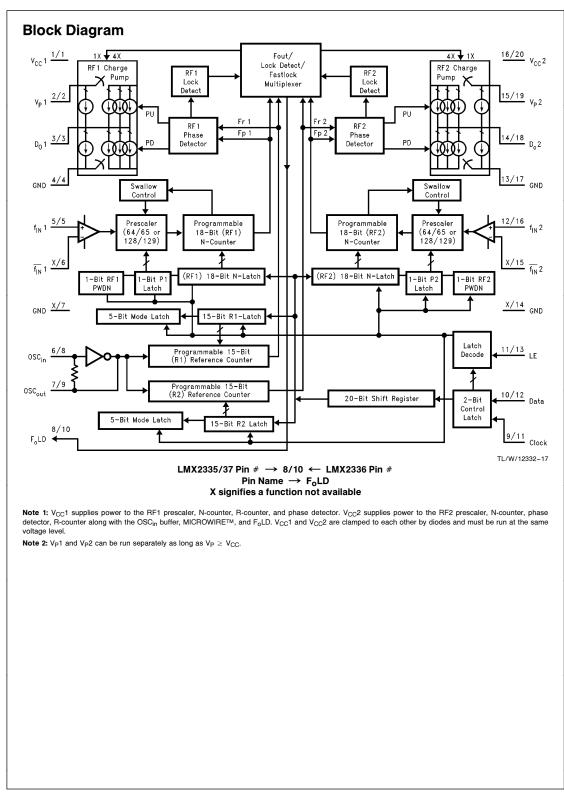
- Cellular telephone systems (AMPS, ETACS, RCR-27) Cordless telephone systems
- (DECT, ISM, PHS, CT-1+)
- Personal Communication Systems (DCS-1800, PCN-1900)
- Dual Mode PCS phones
- CATV
- Other wireless communication systems



Synthesizer for RF Personal Communications .MX2335/LMX2336/LMX2337 **PLLatinum Dual** Frequency

September 1996

Conne		Diagran					
LMX2335/LMX2337				LMX2336			
	Vp 1 Dg 1 GND f _{IN} 1 OSC _{in} OSC _{out} F _o LD	- 6 - 7	11 - L 10 - D 9 - C M/LMX X2337T	$\begin{array}{cccccccccccccccccccccccccccccccccccc$			
	NO I ackage		i ion an	NS Package Number MTC20			
Pin De	escripti	on					
Pin No. 2335/37	Pin No. 2336	Pin Name	1/0	Description			
1	1	V _{CC} 1		Power supply voltage input for RF1 analog and RF1 digital circuits. Input may range from 2.7V to 5.5V. V_{CC} 1 must equal V_{CC} 2. Bypass capacitors should be placed as close as possible to this pin and be connected directly to the ground plane.			
2	2	V _p 1		Power supply for RF1 charge pump. Must be \geq V_CC.			
3	3	D _o 1	0	RF1 charge pump output. For connection to a loop filter for driving the input of an external VCO.			
4	4	GND		LMX2335/37: Ground for RF1 analog and RF1 digital circuits. LMX2336: Ground for RF digital circuitry.			
5	5	f _{IN} 1	I	First RF prescaler input. Small signal input from the VCO.			
Х	6	f _{IN} 1	I	RF1 prescaler complementary input. A bypass capacitor should be placed as close possible to this pin and be connected directly to the ground plane. Capacitor is optional with loss of some sensitivity.			
Х	7	GND		Ground for RF1 analog circuitry.			
6	8	OSC _{in}	I	Oscillator input. The input has a $V_{CC}/2$ input threshold and can be driven from an external CMOS or TTL logic gate.			
7	9	OSCout	0	Oscillator output.			
8	10	F₀LD	0	Multiplexed output of the programmable or reference dividers, lock detect signals ar Fastlock mode. CMOS output (see Programmable Modes).			
9	11	Clock		High impedance CMOS Clock input. Data for the various latches is clocked in on the rising edge, into the 20-bit shift register.			
10	12	Data	I	Binary serial data input. Data entered MSB first. The last two bits are the control bits High impedance CMOS input.			
11	13	LE		Load enable high impedance CMOS input. When LE goes HIGH, data stored in the shift registers is loaded into one of the 4 appropriate latches (control bit dependent)			
Х	14	GND		Ground for RF2 analog circuitry.			
Х	15	f _{IN} 2	I	RF2 prescaler complementary input. A bypass capacitor should be placed as close possible to this pin and be connected directly to the ground plane. Capacitor is optional with loss of some sensitivity.			
12	16	f _{IN} 2	Ι	RF2 prescaler input. Small signal input from the VCO.			
13	17	GND		LMX2335/37: Ground for RF2 analog, RF2 digital, MICROWIRE™, F _o LD and Oscillator circuits. LMX2336: Ground for RF2 digital, MICROWIRE™, F _o LD and Oscillator circuits.			
14	18	D _o 2	0	RF2 charge pump output. For connection to a loop filter for driving the input of an external VCO.			
15	19	V _p 2		Power supply for RF2 charge pump. Must be $\geq V_{CC}.$			
16	20	V _{CC} 2		Power supply voltage input for RF2 analog, RF2 digital, MICROWIRETM, F_0LD and Oscillator circuits. Input may range from 2.7V to 5.5V. $V_{CC}2$ must equal $V_{CC}1$. Bypas capacitors should be placed as close as possible to this pin and be connected direct to the ground plane.			



Absolute Maximum Ratings (1, 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Power Supply Voltage	
V _{CC}	-0.3V to $+6.5V$
VP	-0.3V to $+6.5V$
Voltage on Any Pin	
with $GND = 0V (V_I)$	$-0.3V$ to V_{CC} $+0.3V$
Storage Temperature Range (T _S)	$-65^{\circ}C$ to $+150^{\circ}C$
Lead Temperature (solder 4 sec.) (TL)	+ 260°C

Recommended Operating Conditions

Power Supply Voltage

V _{CC}	
VP	
Operating Temperature (T _A)	

 $\begin{array}{r} \text{2.7V to 5.5V} \\ \text{V}_{\text{CC}} \text{ to } + \text{5.5V} \\ - \text{40^{\circ}C} \text{ to } + \text{85^{\circ}C} \end{array}$

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended Operating Conditions indicate conditions for which the device is intended to be functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed.

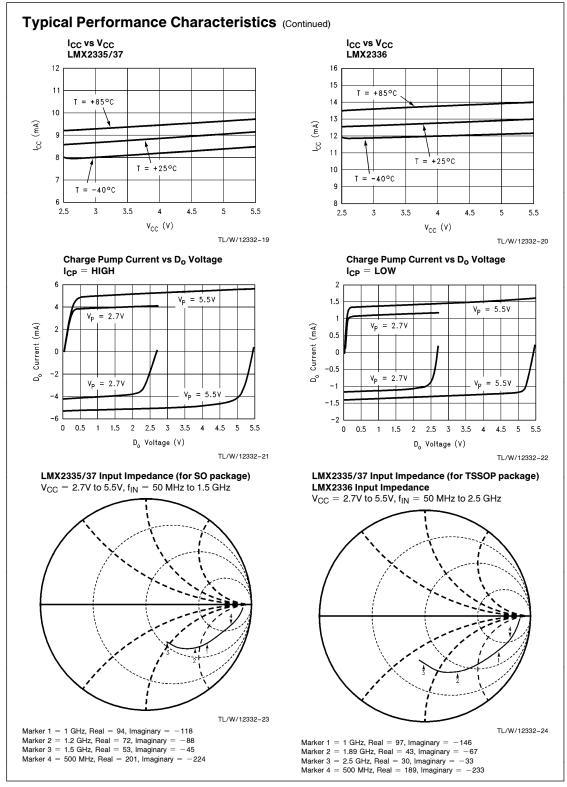
Note 2: This device is a high performance RF integrated circuit with an ESD rating <2 keV and is ESD sensitive. Handling and assembly of this device should only be done at ESD protected workstations.

Electrical Characteristics $V_{CC} = 5.0V$, $V_P = 5.0V$; $T_A = 25^{\circ}C$, except as specified

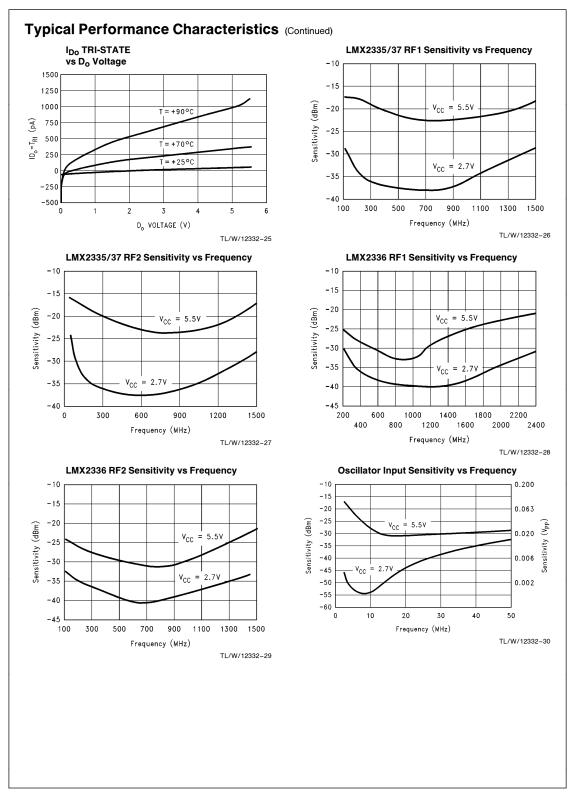
Cumhal	Dave	meter	Conditions		Units		
Symbol	Para	imeter	Conditions	Min	Тур	Max	Units
ICC	Power Supply Current	LMX2335/37 RF1 and RF2	$V_{CC} = 2.7V \text{ to } 5.5V$		10	15	mA
I _{CC}]	LMX2335/37 RF1 only			6	8	mA
ICC		LMX2336 RF1 and RF2			13	18	mA
		LMX2336 RF1 only			7	11	mA
f _{IN} 1	Operating Frequency	LMX2335		0.100		1.1	GHz
f _{IN} 2				0.050		1.1	GHz
f _{IN} 1		LMX2336		0.200		2.0	GHz
f _{IN} 2				0.050		1.1	GHz
f _{IN} 1		LMX2337		100		550	MHz
f _{IN} 2				50		550	MHz
ICC-PWDN	Powerdown Current LMX2335/2336 V _{CC} = 5.5V		$V_{CC} = 5.5V$		1	25	
		LMX2337				100	μA
fosc	Oscillator Frequency		With resonator load on OSCout	5		20	MHz
fosc			No load on OSC _{out}	5		40	MHz
f _φ	Phase Detector Frequ	ency				10	MHz
Pf _{IN} 1 and	RF Input Sensitivity		V _{CC} = 3.0V, f > 100 MHz	-15		+4	
Pf _{IN} 2			V _{CC} = 5.0V, f > 100 MHz	-10		+4	dBm
			$V_{CC}=$ 2.7 to 5.5V, f $>$ 100 MHz	-10		0	
V _{OSC}	Oscillator Sensitivity		OSC _{in}	0.5			V _{PP}
VIH	High-Level Input Volta	ge	**	0.8 V _{CC}			V
VIL	Low-Level Input Voltag	ge	**			0.2 V _{CC}	V
IIH	High-Level Input Curre	ent	$V_{IH} = V_{CC} = 5.5V^{**}$	-1.0		1.0	μA
Ι _{ΙL}	Low-Level Input Curre	nt	$V_{IL} = 0V, V_{CC} = 5.5V^{**}$	-1.0		1.0	μA
Ι _Η	Oscillator Input Currer	ıt	$V_{IH} = V_{CC} = 5.5V$			100	μA
Ι _{ΙL}	Oscillator Input Currer	ıt	$V_{IL} = 0V, V_{CC} = 5.5V$	-100			μA
ID0-SOURCE	Charge Pump Output	Current	$V_{D_0} = V_P/2$, $I_{CP_0} = LOW^*$		-1.25		mA
I _{Do} -SINK			$V_{D_0} = V_P/2$, $I_{CP_0} = LOW^*$		1.25		mA
ID0-SOURCE]		$V_{D_0} = V_P/2$, $I_{CP_0} = HIGH^*$		-5.0		mA
I _{Do} -SINK]		$V_{D_0} = V_P/2$, $I_{CP_0} = HIGH^*$		5.0		mA
I _{Do} -TRI	Charge Pump TRI-STATE Current	LMX2335 LMX2336	$\begin{array}{l} 0.5V \leq V_{D_0} \leq V_P - 0.5V \\ T = 25^\circ C \end{array}$	-5.0		5.0	nA
I _{Do} -TRI	Charge Pump TRI-STATE Current	LMX2337	$\begin{array}{l} 0.5V \leq V_{D_0} \leq V_P - 0.5V \\ T = 25^\circ C \end{array}$		±5		nA

Symbol	Parameter	Conditions	v v	11		
Symbol	Parameter	Conditions	Min	Тур	Мах	Units
V _{OH}	High-Level Output Voltage	$I_{OH} = -500 \ \mu A$	V _{CC} - 0.4			V
V _{OL}	Low-Level Output Voltage	$I_{OL} = 500 \ \mu A$			0.4	V
t _{CS}	Data to Clock Set Up Time	See Data Input Timing	50			ns
t _{CH}	Data to Clock Hold Time	See Data Input Timing	10			ns
t _{CWH}	Clock Pulse Width High	See Data Input Timing	50			ns
t _{CWL}	Clock Pulse Width Low	See Data Input Timing	50			ns
t _{ES}	Clock to Load Enable Set Up Time	See Data Input Timing	50			ns
t _{EW}	Load Enable Pulse Width	See Data Input Timing	50			ns

*See PROGRAMMABLE MODES for I_{CP_0} description. *Clock, Data and LE does not include $f_{IN}1,\,f_{IN}2$ and OSC_in.

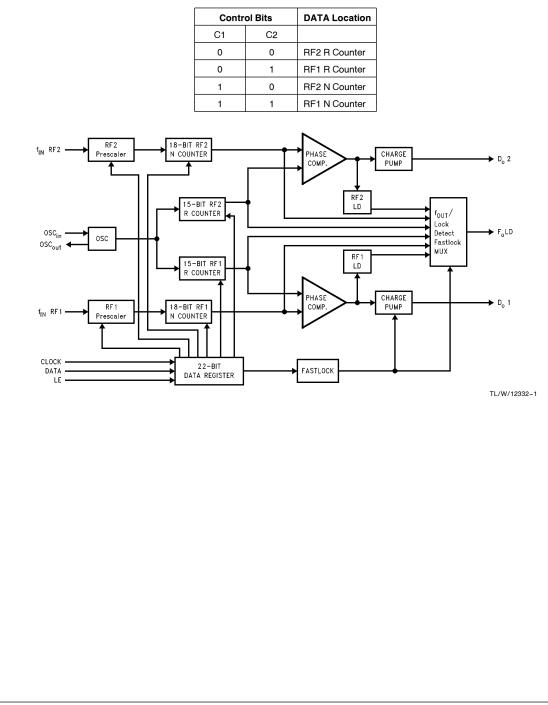


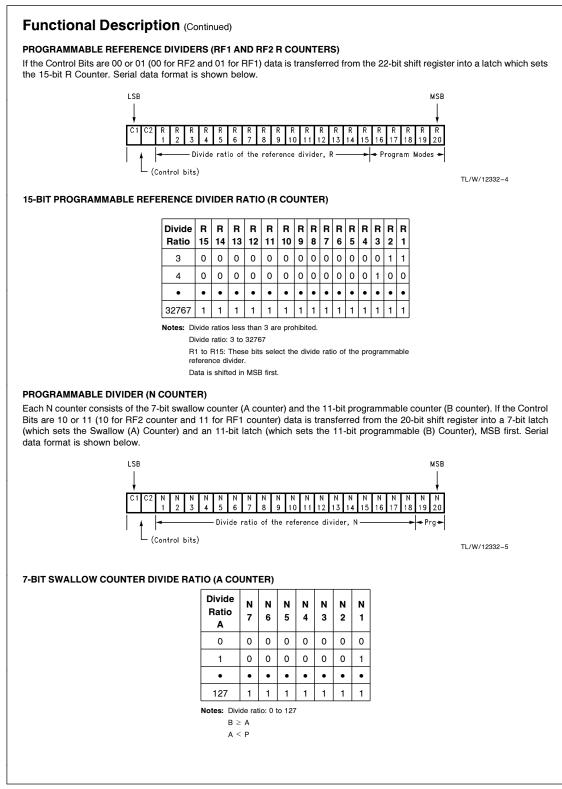
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Functional Description

The simplified block diagram below shows the 22-bit data register, two 15-bit R Counters and two 18-bit N Counters (intermediate latches are not shown). The data stream is clocked (on the rising edge of Clock) into the DATA register, MSB first. The data stored in the shift register is loaded into one of the 4 appropriate latches on the rising edge of LE. The last two bits are the Control Bits. The DATA is transferred into the counters as follows:





Functional Description (Continued)

11-BIT PROGRAMMABLE COUNTER DIVIDE RATIO (B COUNTER)

Divide Ratio B	N 18	N 17	N 16	N 15	N 14	N 13	N 12	N 11	N 10	N 9	N 8
3	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	1	0	0
•	•	٠	٠	٠	•	٠	•	٠	٠	•	•
2047	1	1	1	1	1	1	1	1	1	1	1

Note: Divide ratio: 3 to 2047 (Divide ratios less than 3 are prohibited)

 $B \ge A$

PULSE SWALLOW FUNCTION

 $f_{VCO} = [(P \times B) + A] \times f_{OSC}/R$

f_{VCO}: Output frequency of external voltage controlled oscillator (VCO)

- B: Preset divide ratio of binary 11-bit programmable counter (3 to 2047)
- A: Preset divide ratio of binary 7-bit swallow counter

(0 \leq A \leq P; A \leq B)

f_{OSC}: Output frequency of the external reference frequency oscillator

- R: Preset divide ratio of binary 15-bit programmable reference counter (3 to 32767)
- P: Preset modulus of dual modulus prescaler (P = 64 or 128)

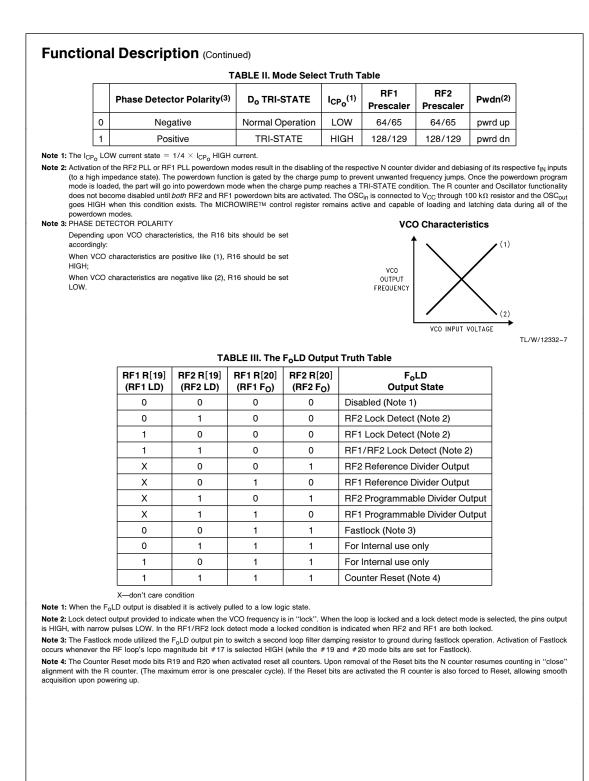
PROGRAMMABLE MODES

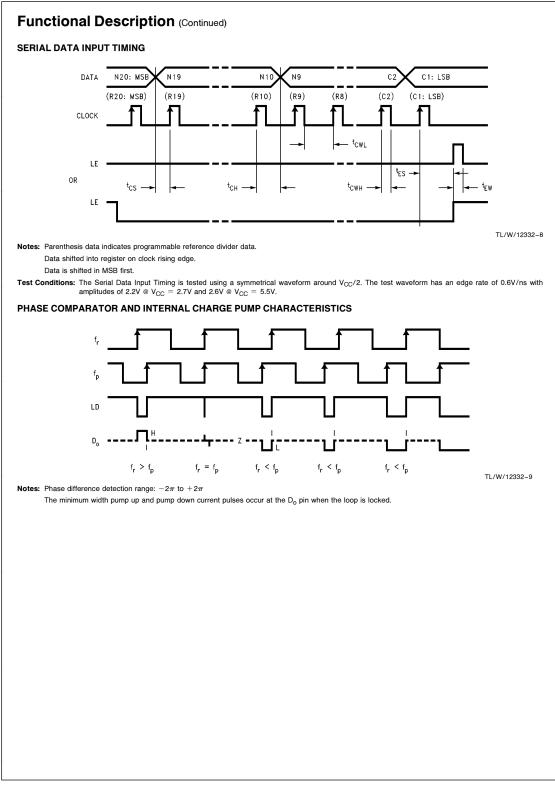
Several modes of operation can be programmed with bits R16–R20 including the phase detector polarity, charge pump tristate and the output of the F_0LD pin. The prescaler and power down modes are selected with bits N19 and N20. The programmable modes are shown in Table I. Truth table for the programmable modes and F_0LD output are shown in Table II and Table III.

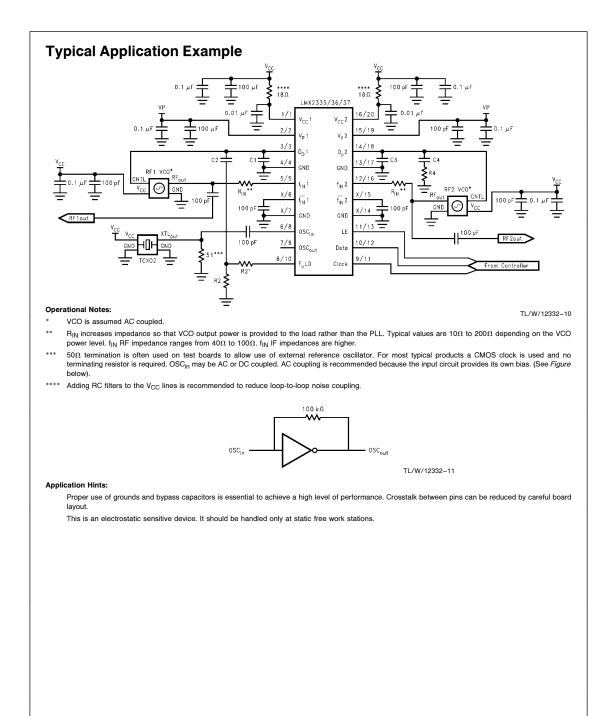
TABLE I	Programmable	Modes
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C1	C2	R16	R17	R18	R19	R20
0	0	RF2 Phase Detector Polarity	RF2 I _{CPo}	RF2 D _o TRI-STATE	RF2 LD	RF2 F _o
0	1	RF1 Phase Detector Polarity	RF1 I _{CPo}	RF1 D _o TRI-STATE	RF1 LD	RF1 F _o

C1	C2	N19	N20
1	0	RF2 Prescaler	Pwdn RF2
1	1	RF1 Prescaler	Pwdn RF1







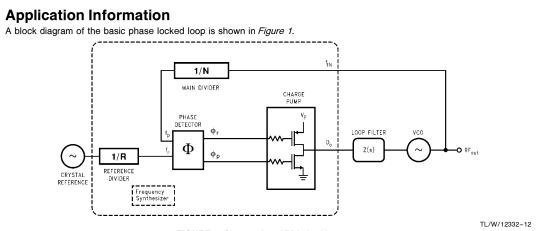
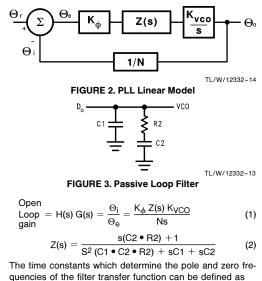


FIGURE 1. Conventional PLL Architecture

Loop Gain Equations

A linear control system model of the phase feedback for a PLL in the locked state is shown in *Figure 2*. The open loop gain is the product of the phase comparator gain (K_{db}), the VCO gain (K_{VCO}/s), and the loop filter gain Z(s) divided by the gain of the feedback counter modulus (N). The passive loop filter configuration used is displayed in *Figure 3*, while the complex impedance of the filter is given in equation 2.



$$T1 = R2 \bullet \frac{C1 \bullet C2}{C1 + C2}$$
(3a)

$$\Gamma 2 = R2 \bullet C2 \tag{3b}$$

The 3rd order PLL Open Loop Gain can be calculated in terms of frequency, ω , the filter time contants T1 and T2, and the design constants K ϕ , K_{VCO}, and N.

$$G(s) \bullet H(s) \bigg|_{s = i \bullet w} = \frac{-K\phi \bullet K_{VCO} (1 + jw \bullet T2)}{w^2 C1 \bullet N (1 + jw \bullet T1)} \bullet \frac{T1}{T2}$$
(4)

From equation 3 we can see that the phase term will be dependent on the single pole and zero such that the phase margin is determined in equation 5.

$$\begin{split} \varphi(\omega) &= \tan^{-1}(\omega \bullet \text{T2}) - \tan^{-1}(\omega \bullet \text{T1}) + 180^\circ\text{C} \end{tabular} \end{split} (5) \\ \text{A plot of the magnitude and phase of G(s) H(s) for a stable loop, is shown in$$
Figure 4 $with a solid trace. The parameter <math>\varphi_p$ shows the amount of phase margin that exists at the point the gain drops below zero (the cutoff frequency wp of the loop). In a critically damped system, the amount of phase margin would be approximately 45 degrees. \end{split}

If we were now to redefine the cut off frequency, wp', as double the frequency which gave us our original loop bandwidth, wp, the loop response time would be approximately halved. Because the filter attenuation at the comparison frequency also diminishes, the spurs would have increased by approximately 6 dB. In the proposed Fastlock scheme, the higher spur levels and wider loop filter conditions would exist only during the initial lock-on phase-just long enough to reap the benefits of locking faster. The objective would be to open up the loop bandwidth but not introduce any additional complications or compromises related to our original design criteria. We would ideally like to momentarily shift the curve Figure 4 over to a different cutoff frequency, illustrated by dotted line, without affecting the relative open loop gain and phase relationships. To maintain the same gain/ phase relationship at twice the original cutoff frequency, other terms in the gain and phase equations 4 and 5 will have to compensate by the corresponding "1/w" or "1/w2" factor. Examination of equations 3 and 5 indicates the damping resistor variable R2 could be chosen to compensate with "w" terms for the phase margin. This implies that another resistor of equal value to R2 will need to be switched in parallel with R2 during the initial lock period. We must also insure that the magnitude of the open loop gain, H(s)G(s) is equal to zero at wp' = 2 wp. K_{VCO}, K ϕ , N, or the net product of these terms can be changed by a factor of 4, to counteract with w² term present in the denominator of

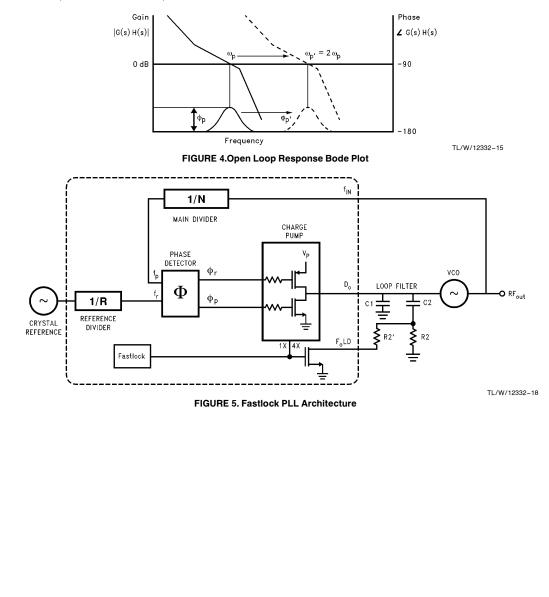
Application Information (Continued)

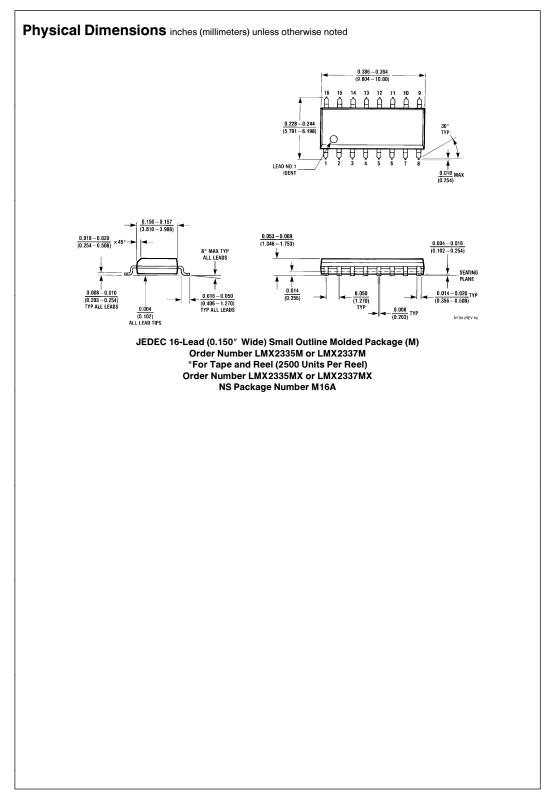
equation 3. The K ϕ term was chosen to complete the transformation because it can readily be switched between 1X and 4X values. This is accomplished by increasing the charge pump output current from 1 mA in the standard mode to 4 mA in Fastlock.

Fastlock Circuit Implementation

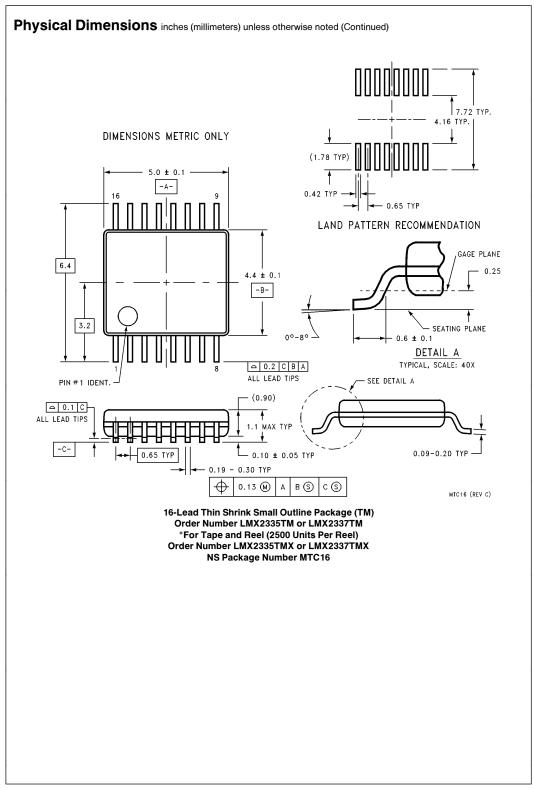
A diagram of the Fastlock scheme as implemented in National Semiconductors LMX2335/36/37 PLL is shown in *Figure 5*. When a new frequency is loaded, and the RF1 I_{CPo} bit is set high, the charge pump circuit receives an input to deliver 4 times the normal current per unit phase error while an open drain NMOS on chip device switches in a

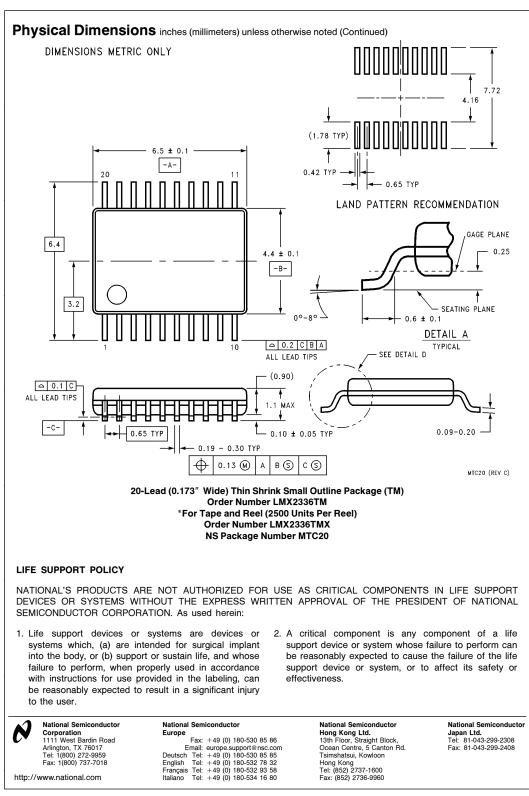
second R2 resistor element to ground. The user calculates the loop filter component values for the normal steady state considerations. The device configuration ensures that as long as a second identical damping resistor is wired in appropriately, the loop will lock faster without any additional stability considerations to account for. Once locked on the correct frequency, the user can return the PLL to standard low noise operation by sending a MICROWIRE instruction with the RF1 $_{\rm CPO}$ bit set low. This transition does not affect the charge on the loop filter capacitors and is enacted synchronous with the charge pump output. This creates a nearly seamless change between Fastlock and standard mode.











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